

# **Excellent Integrated System Limited**

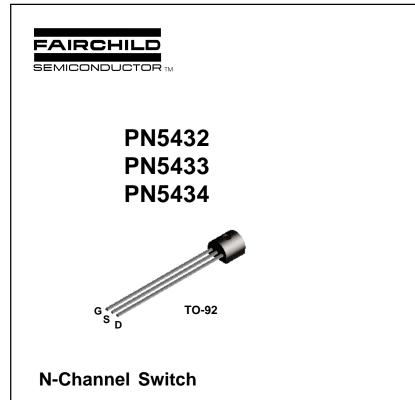
Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

Fairchild Semiconductor PN5434

For any questions, you can email us directly: <u>sales@integrated-circuit.com</u>





This device is designed for analog or digital switching applications where very low On Resistance is mandatory. Sourced from Process 58. See J108 for characteristics.

#### Absolute Maximum Ratings\* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>DG</sub>	Drain-Gate Voltage	25	V
V <sub>GS</sub>	Gate-Source Voltage	-25	V
$I_{GF}$	Forward Gate Current	10	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## **Thermal Characteristics**

Symbol	Characteristic	Max	Units
		PN5432 / 5433 / 5434	1
P <sub>D</sub>	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
R <sub>θJC</sub>	Thermal Resistance, Junction to Case	125	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

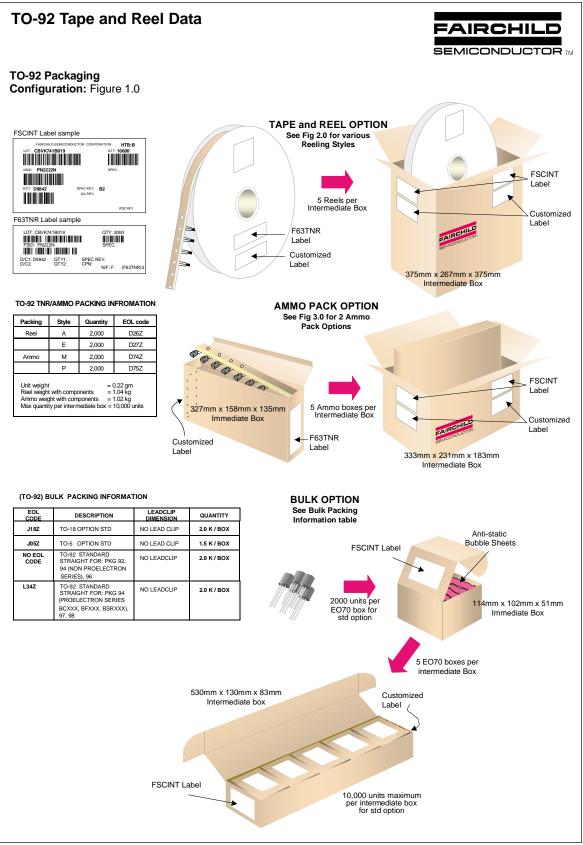
TA = 25°C unless otherwise noted

©2001 Fairchild Semiconductor Corporation



Parameter	Test Conditions		Min	Max	Units
RACTERISTICS					1
° °			-25		V
Gate Reverse Current		°C		-200 -200	pA nA
Drain Cutoff Leakage Voltage	$V_{GS} = 10 \text{ V}, V_{DS} = 5.0 \text{ V},$	0		-200	pА
Cata Source Cutoff Voltage	$I_A = 150 ^{\circ}\text{C}$	5422	4.0		nA V
Cale-Ource Culon Vollage	$v_{\rm DS} = 3.0 v, v_{\rm D} = 3.0 \text{ IA}$	5432 5433	-4.0 -3.0	-10 -9.0	V
		5434	-1.0	-4.0	V
ACTERISTICS					
Zero-Gate Voltage Drain Current*	$V_{DS} = 15 V, V_{GS} = 0$	5432	150		mA
					mA mA
Drain-Source On Voltage	$I_{\rm D} = 10 \text{ mA}$ . $V_{\rm GS} = 0$		50	50	mV
g-		5433		70	mV
		5434		100	mV
Drain-Source On Resistance	$I_{\rm D} = 10  \text{mA},  V_{\rm GS} = 0$		2.0		Ω
					Ω Ω
	$I_D = 0, V_{GS} = 0, f = 1.0 \text{ kHz}$	• •• •			32
		5432	2.0	5.0	Ω
					Ω
		3434		10	Ω
GNAL CHARACTERISTICS					
Input Capacitance				30	pF
Reverse Transfer Capacitance	$V_{DS} = 0$ , $V_{GS} = 10$ V, f = 1.0	MHz		15	pF
					1
NG CHARACTERISTICS					ns
Delay Time	$V_{DD} = 1.5 V, V_{GS(on)} = 0,$			4.0	
Delay Time Rise Time	I <sub>D(on)</sub> = 10 mA			4.0 1.0	ns
Delay Time	$I_{D(on)} = 10 \text{ mA}$ $V_{GS(off)} = 12 \text{ V},$	5400		1.0	ns
Delay Time Rise Time	$ I_{D(on)} = 10 \text{ mA} V_{GS(off)} = 12 \text{ V}, V_{DS(on)} = 50 \text{ mV} $	5432 5433			
Delay Time Rise Time	$I_{D(on)} = 10 \text{ mA}$ $V_{GS(off)} = 12 \text{ V},$	5432 5433 5434		1.0 6.0	ns ns
	RACTERISTICS         Gate-Source Breakdown Voltage         Gate Reverse Current         Drain Cutoff Leakage Voltage         Gate-Source Cutoff Voltage         Gate-Source Cutoff Voltage         ACTERISTICS         Zero-Gate Voltage Drain Current*         Drain-Source On Voltage         Drain-Source On Resistance	RACTERISTICSGate-Source Breakdown VoltageI_G = 1.0 $\mu$ A, V_DS = 0Gate Reverse Current $V_{GS} = 15 V, V_{DS} = 0$ $V_{GS} = 15 V, V_{DS} = 0, T_A = 150$ Drain Cutoff Leakage Voltage $V_{GS} = 10 V, V_{DS} = 5.0 V$ $V_{GS} = 10 V, V_{DS} = 5.0 V, T_A = 150 °C$ Gate-Source Cutoff Voltage $V_{DS} = 5.0 V, I_D = 3.0 nA$ ACTERISTICSZero-Gate Voltage Drain Current* $V_{DS} = 15 V, V_{GS} = 0$ Drain-Source On Voltage $I_D = 10 mA, V_{GS} = 0$ Drain-Source On Resistance $I_D = 10 mA, V_{GS} = 0$ $I_D = 0, V_{GS} = 0, f = 1.0 kHz$ GNAL CHARACTERISTICSInput Capacitance $V_{DS} = 0, V_{GS} = 10 V, f = 1.0 I$	RACTERISTICS           Gate-Source Breakdown Voltage $I_G = 1.0 \ \mu A, V_{DS} = 0$ Gate Reverse Current $V_{GS} = 15 \ V, V_{DS} = 0$ $V_{GS} = 15 \ V, V_{DS} = 0, T_A = 150 \ ^{\circ}C$ Drain Cutoff Leakage Voltage $V_{GS} = 10 \ V, V_{DS} = 5.0 \ V$ $V_{GS} = 10 \ V, V_{DS} = 5.0 \ V, I_D = 3.0 \ nA$ 5432           Gate-Source Cutoff Voltage $V_{DS} = 5.0 \ V, I_D = 3.0 \ nA$ 5432           ACTERISTICS         Zero-Gate Voltage Drain Current* $V_{DS} = 15 \ V, V_{GS} = 0$ 5432           Jorain-Source On Voltage $I_D = 10 \ mA, V_{GS} = 0$ 5432           Drain-Source On Resistance $I_D = 10 \ mA, V_{GS} = 0$ 5432           Mathematical State $I_D = 10 \ mA, V_{GS} = 0$ 5432           GNAL CHARACTERISTICS         Input Capacitance $V_{DS} = 0, V_{GS} = 10 \ V, f = 1.0 \ MHz$	RACTERISTICS           Gate-Source Breakdown Voltage $I_G = 1.0 \ \mu A, V_{DS} = 0$ -25           Gate Reverse Current $V_{GS} = 15 \ V, V_{DS} = 0$ $V_{GS} = 15 \ V, V_{DS} = 0, T_A = 150 \ ^{\circ}C$ Drain Cutoff Leakage Voltage $V_{GS} = 10 \ V, V_{DS} = 5.0 \ V, V_{DS} = 5.0 \ V, V_{DS} = 5.0 \ V, V_{DS} = 10 \ V, V_{DS} = 5.0 \ V, V_{DS} = 1.0 \ V, V_{DS} = 5.0 \ V, V_{DS} = 1.0 \ V, V_{DS} = 5.0 \ V, V_{DS} = 5.0 \ V, V_{DS} = 5.0 \ V, V_{DS} = 1.0 \ V, V_{DS} = 5.0 \ V, V_{DS} = 5.0 \ V, V_{DS} = 10 \ V, f = 1.0 \ MHz$	RACTERISTICS           Gate-Source Breakdown Voltage $I_G = 1.0 \ \mu A, V_{DS} = 0$ -25           Gate Reverse Current $V_{GS} = 15 \ V, V_{DS} = 0$ -200 $V_{GS} = 15 \ V, V_{DS} = 0, T_A = 150 \ ^{\circ}C$ -200           Drain Cutoff Leakage Voltage $V_{GS} = 10 \ V, V_{DS} = 5.0 \ V, V_{DS} = 1.0 \ V_{DS} = 0.0 \ S_{4333} \ V_{DS} = 1.0 \ S_{4334} \ V_{DS} = 1.0 \ S_{4334} \ V_{DS} = 0 \ S_{4334} \ V_{DS} \ S_{4334} \ V_{DS} = 0 \ S_{4334} \ V_{DS} = 0 \ S_{4334} \ V_{DS} \ S_{4334} \ S_{2.0} \ S_{2.0}$

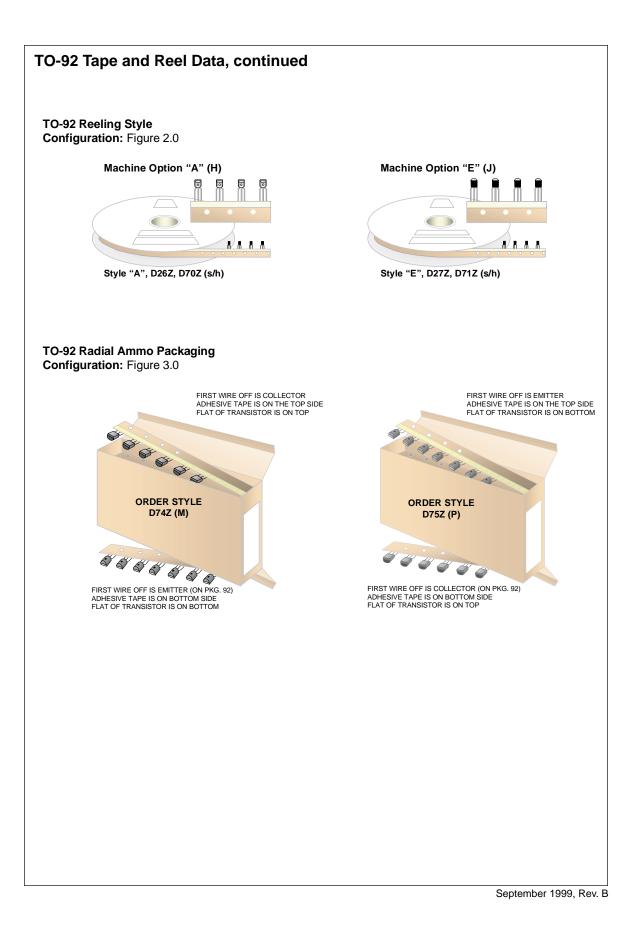




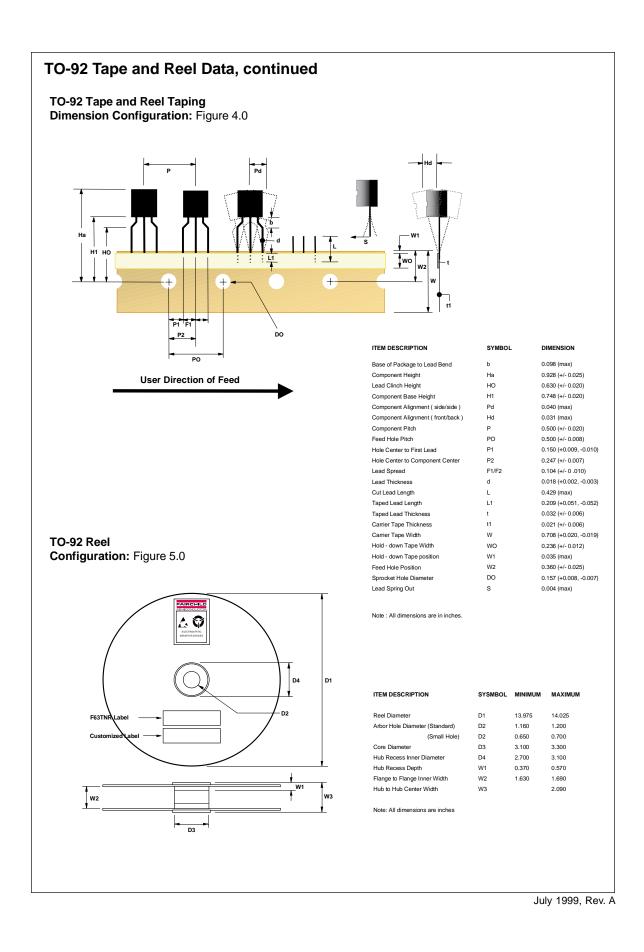
©2001 Fairchild Semiconductor Corporation

March 2001, Rev. B1

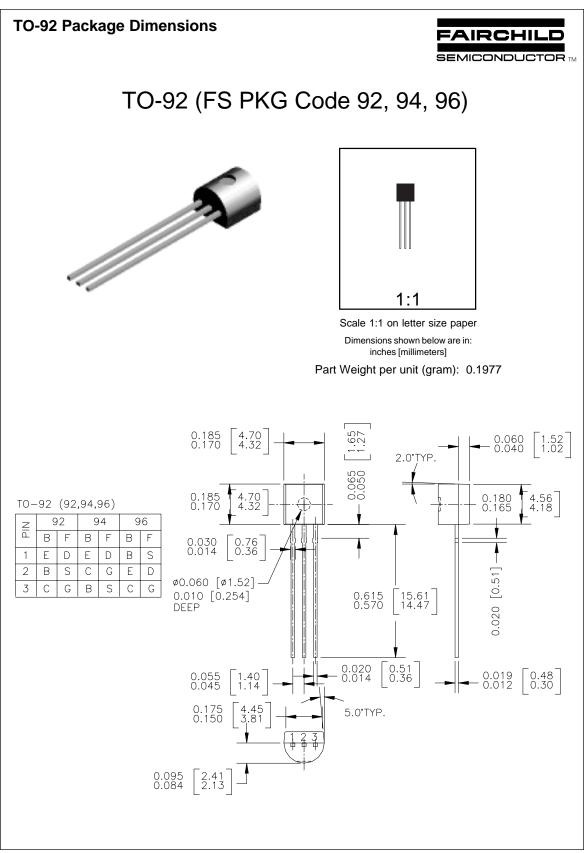












©2000 Fairchild Semiconductor International

January 2000, Rev. B



TRADEMARKS			
and unregistered trademarks Fail stive list of all such trademarks.	rchild Semiconductor owns or is at	uthorized to use and is	
FAST ®	OPTOPLANAR™	SuperSOT™-3	
FASTr™	PACMAN™	SuperSOT™-6	
FRFET™	POP™	SuperSOT™-8	
GlobalOptoisolator™	PowerTrench <sup>®</sup>	SyncFET™	
GTO™	QFET™	TinyLogic™	
HiSeC™	QS™	UHC™	
ISOPLANAR™	QT Optoelectronics <sup>™</sup>	<b>UltraFET</b> ®	
LittleFET™	Quiet Series <sup>™</sup>	VCX™	
MicroFET™	SILENT SWITCHER <sup>®</sup>		
MICROWIRE™	SMART START™		
OPTOLOGIC™	Stealth™		
	stive list of all such trademarks. FAST <sup>®</sup> FASTr <sup>™</sup> FRFET <sup>™</sup> GlobalOptoisolator <sup>™</sup> GTO <sup>™</sup> HiSeC <sup>™</sup> ISOPLANAR <sup>™</sup> LittleFET <sup>™</sup> MicroFET <sup>™</sup> MICROWIRE <sup>™</sup>	FAST ®OPTOPLANARTMFASTrTMPACMANTMFRFETTMPOPTMGlobalOptoisolatorTMPowerTrench ®GTOTMQFETTMHiSeCTMQSTMISOPLANARTMQT OptoelectronicsTMLittleFETTMQuiet SeriesTMMicroFETTMSILENT SWITCHER ®MICROWIRETMSMART STARTTM	

### DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

#### LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user. 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

### **PRODUCT STATUS DEFINITIONS**

#### Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.
	•	Rev. H2